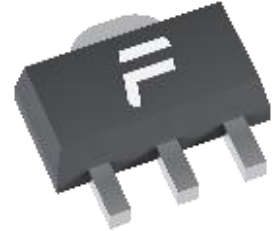
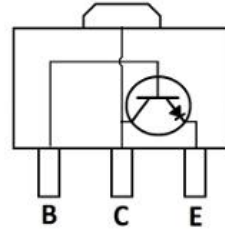


SOT-89-3L Bipolar Transistor 双极型三极管



■ Features 特点

NPN High Voltage 高压



■ Absolute Maximum Ratings 最大额定值

Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Collector-Base Voltage 集电极基极电压	$V_{CBO}$	160	V
Collector-Emitter Voltage 集电极发射极电压	$V_{CEO}$	160	V
Emitter-Base Voltage 发射极基极电压	$V_{EBO}$	6	V
Collector Current 集电极电流	$I_C$	1000	mA
Power dissipation 耗散功率	$P_C(T_a=25^\circ\text{C})$	500	mW
Thermal Resistance Junction-Ambient 热阻	$R_{\theta JA}$	250	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature 结温和储藏温度	$T_J, T_{stg}$	-55to+150 $^\circ\text{C}$	

■ Device Marking 产品打标

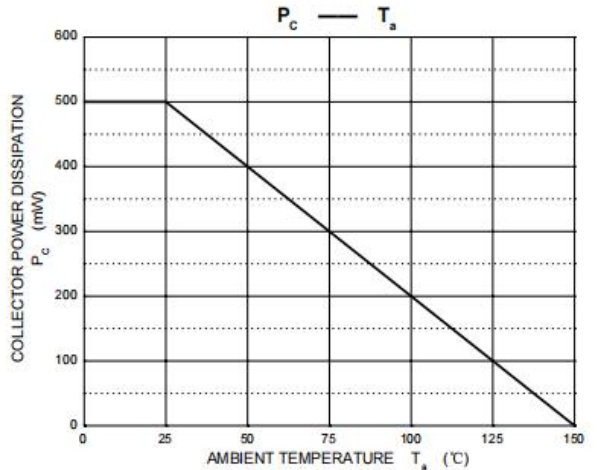
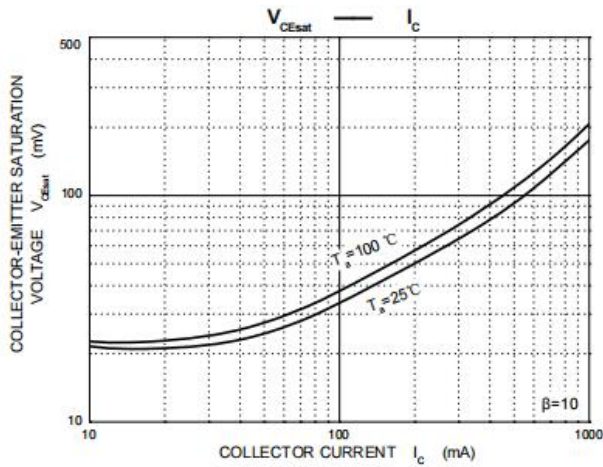
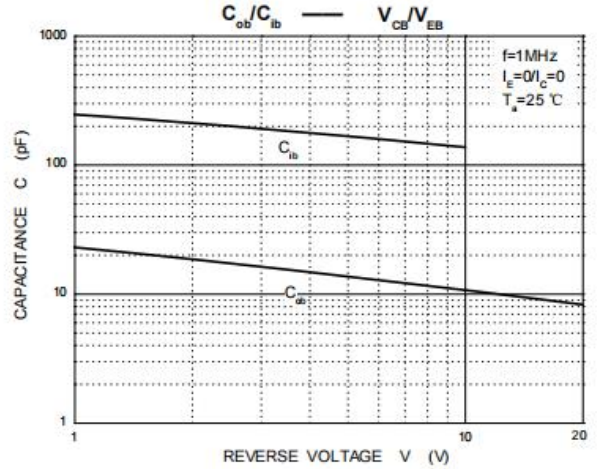
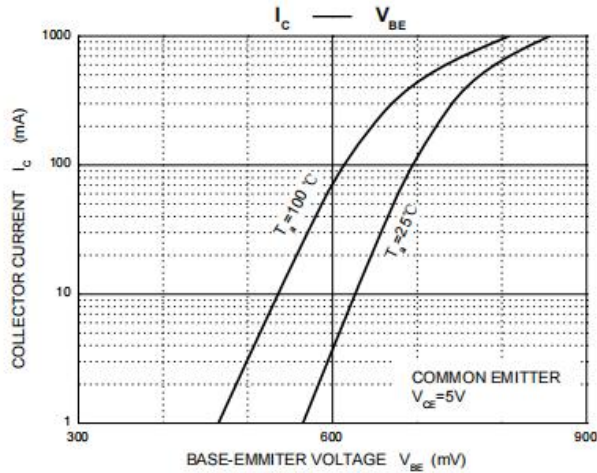
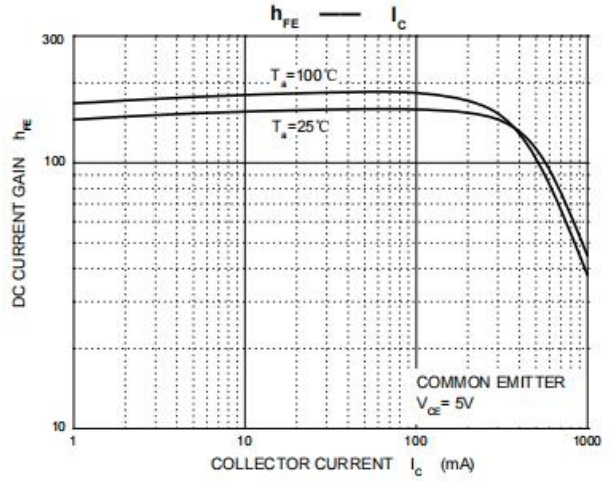
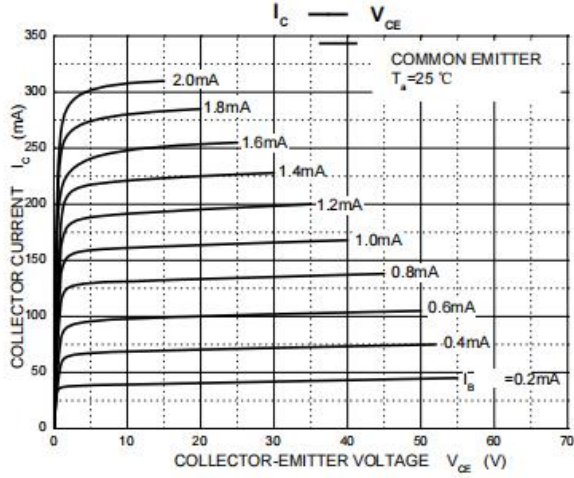
$H_{FE}(1)$	60-120(R)	100-200(O)	160-320(Y)
Mark	2383R	2383O	2383Y

**■ Electrical Characteristics 电特性**

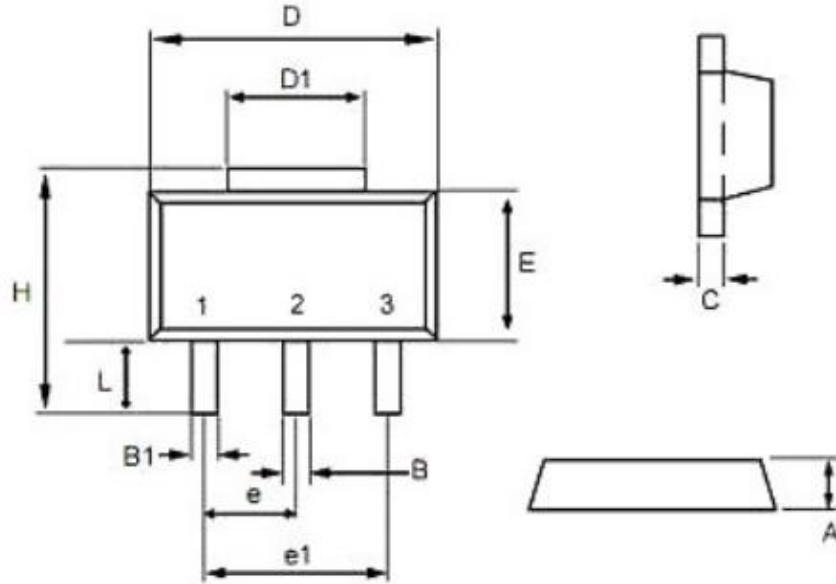
 (T<sub>A</sub>=25°C unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Type 典型值	Max 最大值	Unit 单位
Collector-Base Breakdown Voltage 集电极基极击穿电压(I <sub>C</sub> =100uA, I <sub>E</sub> =0)	BV <sub>CBO</sub>	160	—	—	V
Collector-Emitter Breakdown Voltage 集电极发射极击穿电压(I <sub>C</sub> =1mA, I <sub>B</sub> =0)	BV <sub>CEO</sub>	160	—	—	V
Emitter-Base Breakdown Voltage 发射极基极击穿电压(I <sub>E</sub> =10uA, I <sub>C</sub> =0)	BV <sub>EBO</sub>	6	—	—	V
Collector-Base Leakage Current 集电极基极漏电流(V <sub>CB</sub> =150V, I <sub>E</sub> =0)	I <sub>CBO</sub>	—	—	1	μA
Collector-Emitter Leakage Current 集电极发射极漏电流(V <sub>CE</sub> =150V, R <sub>EB</sub> =10MΩ)	I <sub>CER</sub>	—	—	10	μA
Emitter-Base Leakage Current 发射极基极漏电流(V <sub>EB</sub> =6V, I <sub>C</sub> =0)	I <sub>EBO</sub>	—	—	1	μA
DC Current Gain 直流电流增益(V <sub>CE</sub> =5V, I <sub>C</sub> =200mA)	H <sub>FE</sub> (1)	60	—	320	
DC Current Gain 直流电流增益(V <sub>CE</sub> =5V, I <sub>C</sub> =10mA)	H <sub>FE</sub> (2)	40	—	—	
Collector-Emitter Saturation Voltage 集电极发射极饱和压降(I <sub>C</sub> =500mA, I <sub>B</sub> =50mA)	V <sub>CE(sat)</sub>	—	—	1	V
Base-Emitter Saturation Voltage 基极发射极饱和压降(V <sub>CE</sub> =5V, I <sub>C</sub> =5mA)	V <sub>BE</sub>	—	—	0.75	V
Transition Frequency 特征频率(V <sub>CE</sub> =5V, I <sub>C</sub> =200mA)	f <sub>T</sub>	20	—	—	MHz
Output Capacitance 输出电容(V <sub>CB</sub> = 5V, I <sub>E</sub> =0, f=1MHz)	C <sub>ob</sub>	—	12	—	pF

■ Typical Characteristic Curve 典型特性曲线



■Dimension 外形封装尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.40	1.60	0.055	0.063
B	0.40	0.56	0.016	0.022
B1	0.35	0.48	0.014	0.019
C	0.35	0.44	0.014	0.017
D	4.40	4.60	0.173	0.181
D1	1.35	1.83	0.053	0.072
e	1.45	1.55	0.057	0.061
e1	2.95	3.05	0.116	0.120
E	2.29	2.60	0.090	0.102
H	3.75	4.25	0.148	0.167
L	0.80	1.20	0.031	0.047